



DMTH4005SPSQ

POWERDI

Product Summary

BV _{DSS}	R _{DS(ON)} Max I _D T _C = +25°C (Note 10)	
40V	$3.7 m\Omega @ V_{GS} = 10V$	100A

Features

Rated to +175°C - Ideal For High Ambient Temperature Environments

40V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET

- 100% Unclamped Inductive Switching Ensures More Reliable And Robust End Application
- Low RDS(ON) Minimizes Power Losses
- Low Q_a Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Case Material: Molded Plastic, "Green" Molding Compound.

Terminal Finish - Matte Tin Annealed over Copper Leadframe.

PPAP Capable (Note 4)

Case: POWERDI[®]5060-8

Mechanical Data

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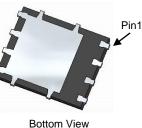
Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Engine Management Systems
- **Body Control Electronics**
- **DC-DC** Converters

Top View





POWERDI[®]5060-8

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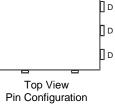
UL Flammability Classification Rating 94V-0

Moisture Sensitivity: Level 1 per J-STD-020

Weight: 0.097 grams (Approximate)

Solderable per MIL-STD-202, Method 208 (e3)

Internal Schematic



ПD

Ordering Information (Note 5)

	Part Number	Case	Packaging			
	DMTH4005SPSQ-13	POWERDI [®] 5060-8	2,500 /Tape & Reel			
Notes:	Notes: 1 EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied					

1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

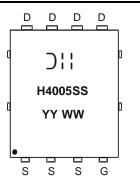
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. For more information, please refer to

http://www.diodes.com/product compliance definitions.html.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



) | | = Manufacturer's Marking H4005SS = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 14 = 2014) WW = Week (01 to 53)

POWERDI is a registered trademark of Diodes Incorporated.



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	40	V	
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Drain Current (Note 6)	T _A = +25°C T _A = +70°C	ID	20.9 17.5	А
Continuous Drain Current (Notes 7 & 10)	T _C = +25°C T _C = +100°C	I _D	100 100	А
Maximum Continuous Body Diode Forward Current (Note 7)		Is	100	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	150	A
Avalanche Current, L=0.6mH		I _{AS}	21	A
Avalanche Energy, L=0.6mH		E _{AS}	132.3	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	T _A = +25°C	PD	2.6	W
Thermal Resistance, Junction to Ambient (Note 6)		R _{0JA}	57	°C/W
Total Power Dissipation (Note 7)	T _C = +25°C	PD	150	W
Thermal Resistance, Junction to Case (Note 7)		R _{0JC}	1	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +175	°C

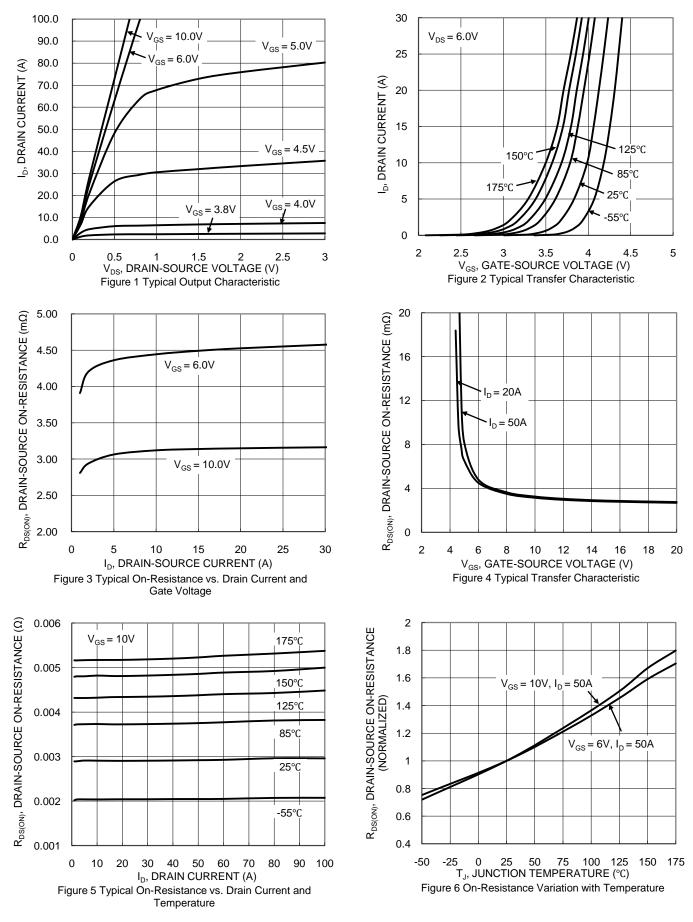
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	40			V	$V_{GS} = 0V, I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	_		1	μA	$V_{DS} = 32V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}			±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)				-	-		
Gate Threshold Voltage	V _{GS(TH)}	2		4	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}		2.9	3.7	mΩ	$V_{GS} = 10V, I_D = 50A$	
Diode Forward Voltage	V _{SD}		0.88		V	$V_{GS} = 0V, I_{S} = 50A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}		3,062			$V_{DS} = 20V, V_{GS} = 0V,$ f = 1MHz	
Output Capacitance	C _{oss}	_	902.2		pF		
Reverse Transfer Capacitance	C _{rss}		179.2				
Gate Resistance	Rg		0.67		Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge	Qg		49.1			$V_{DD} = 20V, I_D = 50A,$ $V_{GS} = 10V$	
Gate-Source Charge	Q _{gs}		10.3		nC		
Gate-Drain Charge	Q _{gd}		13			VGS - 10V	
Turn-On Delay Time	t _{D(ON)}		8.7			$V_{DD} = 20V, V_{GS} = 10V,$ $I_D = 50A, R_G = 3\Omega$	
Turn-On Rise Time	t _R	_	6.8				
Turn-Off Delay Time	t _{D(OFF)}		18.6		ns		
Turn-Off Fall Time	tF		7.3				
Body Diode Reverse Recovery Time	t _{RR}		31.8		ns		
Body Diode Reverse Recovery Charge	Q _{RR}		26.5	İ	nC	I _F = 50A, di/dt = 100A/μs	

 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
7. Thermal resistance from junction to soldering point (on the exposed drain pad).
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.
10. Package limited. Notes:



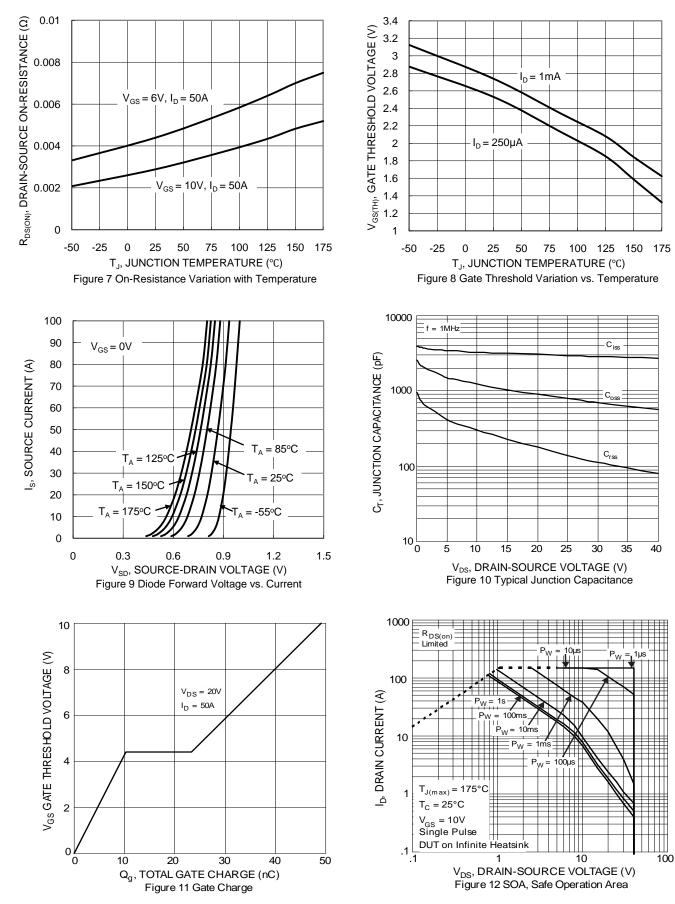
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DMTH4005SPSQ Document number: DS38159 Rev.1 - 2

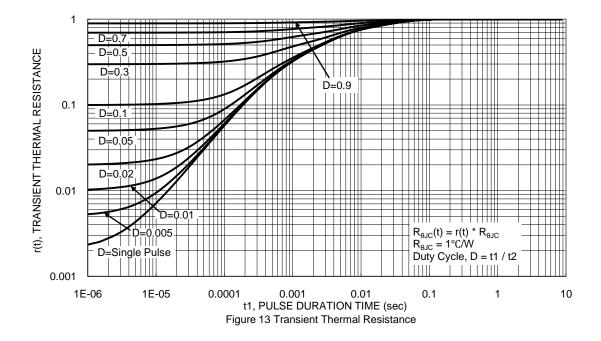


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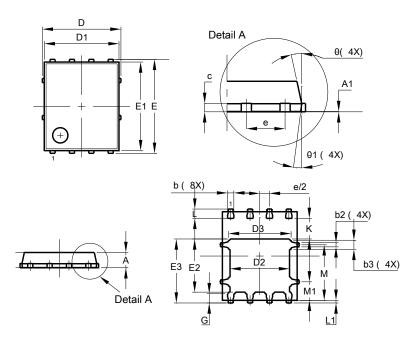






Package Outline Dimensions

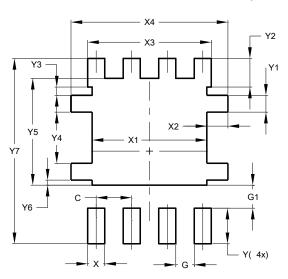
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



1		-@)					
	POWERDI [®] 5060-8						
Dim	Min	Max	Тур				
Α	0.90	1.10	1.00				
A1	0.00	0.05	-				
b	0.33	0.51	0.41				
b2	0.200	0.350	0.273				
b3	0.40	0.80	0.60				
С	0.230	0.330	0.277				
D	4	5.15 BSC					
D1	4.70	5.10	4.90				
D2	3.70	4.10	3.90				
D3	3.90	4.30	4.10				
E	(6.15 BSC					
E1	5.60	6.00	5.80				
E2	3.28	3.68	3.48				
E3	3.99	4.39 4.19					
е		1.27 BSC					
G	0.51	0.71 0.61					
К	0.51						
L	0.51	0.71 0.61					
L1	0.100	0.200	0.175				
М	3.235	4.035	3.635				
M1	1.00	1.40	1.21				
Θ	10º	12º	11 ⁰				
Θ1	6°	8°	7 ⁰				
AI	All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



POWERDI®5060-8

Dimensions	Value (in mm)			
С	1.270			
G	0.660			
G1	0.820			
Х	0.610			
X1	4.100			
X2	0.755			
X3	4.420			
X4	5.610			
Y	1.270			
Y1	0.600			
Y2	1.020			
Y3	0.295			
Y4	1.825			
Y5	3.810			
Y6	0.180			
Y7	6.610			



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